

Silicon NPN Power Transistors

2SD1148

DESCRIPTION

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- With TO-3P(I) package
- Complement to type 2SB863

APPLICATIONS

- Power amplifier applications
- Recommend for 70W high fidelity audio frequency amplifier output stage

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

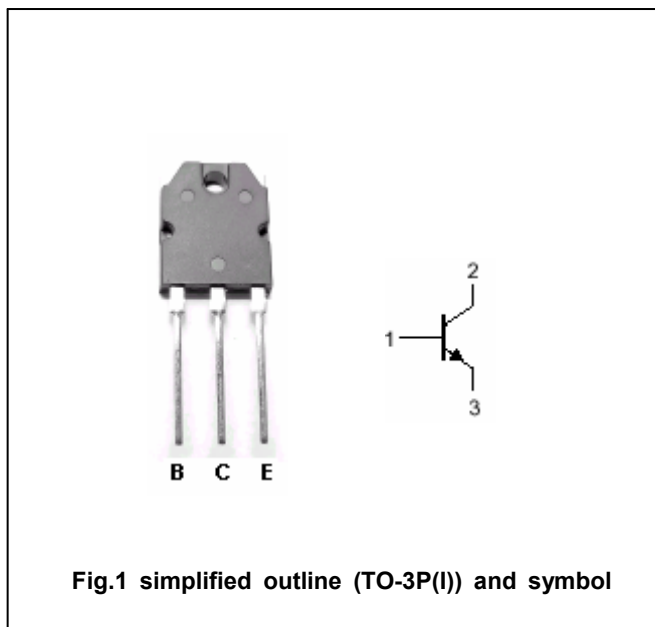


Fig.1 simplified outline (TO-3P(I)) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	140	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	140	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		10	A
I <sub>B</sub>	Base current		1	A
P <sub>T</sub>	Total power dissipation	T <sub>C</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Base-emitter breakdown voltage	I <sub>C</sub> =50mA, I <sub>B</sub> =0	140			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =5A; I <sub>B</sub> =0.5A			2.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =5A; V <sub>CE</sub> =5V			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =140V; I <sub>E</sub> =0			5	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			5	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A; V <sub>CE</sub> =5V	55		160	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =5A; V <sub>CE</sub> =5V	25			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =1A; V <sub>CE</sub> =10V		20		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =10V; f=1MHz		200		pF

◆ h<sub>FE-1</sub> Classifications

R	O
55-110	80-160

